HEX NON-INVERTING TRI-STATE BUFFER

GENERAL DESCRIPTION

The MMC 4503 is a hex non-inverting TRI-STATE buffer with high output current sink and source capability. TRI-STATE outputs make it useful in bus oriented applications. Two separate disable inputs are provided. Buffers 1 to 4 are controlled by the disable A input. Buffers 5 and 6 are controlled by the disable B input. A high level on either disable input will cause those gates on its control line to go into a high impedance state.

FEATURES

- Wide supply voltage range 3.0 V_{DC} to 18 V_{DC}
- TRI-STATE outputs
- Symmetrical turn on/turn off delays
- Symmetrical output rise and fall times
- 1 TTL-load output drive capability
- 2 output-disable controls
- 100% tested for quiescent current

ABSOLUTE MAXIMUM RATINGS

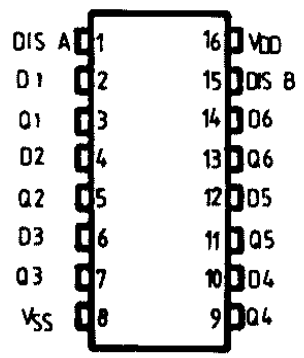
V_{DD}*	Supply voltage: G and H types	-0.5 to	20	V
	E and F types	-0.5 to	18	V
V_i	Input voltage	-0.5 to	V_{DD}+0.5	V
I_i	DC input current (any one input)		±10	mA
P_{tot}	Total power dissipation (per package)		200	mW
	Dissipation per output transistor for T_A = full package-temperature range		100	mW
T_A	Operating temperature : G and H types	-55 to	125	°C
	E and F types	-40 to	85	°C
T_{stg}	Storage temperature	-65 to	150	°C

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

V_{DD}*	Supply voltage: G and H types	3 to	18	V
	E and F types	3 to	15	V
V_i	Input voltage	0 to	V_{DD}	V
T_A	Operating temperature : G and H types	-55 to	125	°C
	E and F types	-40 to	85	°C

CONNECTION DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS

(over recommended operating conditions)

PARAMETER			TEST CONDITIONS				VALUES							UNIT
			V_I (V)	V_O (V)	$\|I_O\|$ (μA)	V_{DD} (V)	T_{LOW}		25°C			T_{HIGH}		
							min.	max.	min.	typ	max.	min.	max.	
I_L	Quiescent current	G, H types	0/ 5			5		1		0.02	1		30	μA
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		E, F types	0/ 5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
			0/15			15		16		0.02	16		120	
V_{OH}	Output high voltage		0/ 5		< 1	5	4.95		4.95			4.95		V
			0/10		< 1	10	9.95		9.95			9.95		
			0/15		< 1	15	14.95		14.95			14.95		
V_{OL}	Output low voltage		5 /0		< 1	5		0.05			0.05		0.05	V
			10/0		< 1	10		0.05			0.05		0.05	
			15/0		< 1	15		0.05			0.05		0.05	
V_{IH}	Input high voltage			0.5/4.5	< 1	5	3.5		3.5			3.5		V
				1/9	< 1	10	7		7			7		
				1.5/13.5	< 1	15	11		11			11		
V_{IL}	Input low voltage			4.5/0.5	< 1	5		1.5			1.5		1.5	V
				9/1	< 1	10		3			3		3	
				13.5/1.5	< 1	15		4			4		4	
I_{OH}	Output drive current	G, H types	0/ 5	2.5		5	-5.8		-4.8	-6.1		-3		mA
			0/ 5	4.6		5	-1.2		-1.02	-1.9		-0.7		
			0/10	9.5		10	-3.1		-2.6	-3.7		-1.8		
			0/15	13.5		15	-8.2		-6.8	-14.1		-4.8		
		E, F types	0/ 5	2.5		5	-4.8		-4.1	-5.2		-2.9		
			0/ 5	4.6		5	-1		-0.8	-1.6		-0.6		
			0/10	9.5		10	-2.5		-2.2	-3.1		-1.6		
			0/15	13.5		15	-6.8		-5.8	-11.9		-4.2		
I_{OL}	Output sink current	G, H types	0/ 5	0.4		5	2.6		2.1	2.3		1.3		mA
			0/10	0.5		10	6.5		5.5	2.6		3.8		
			0/15	1.5		15	19.2		16.1	23		11.2		
		E, F types	0/ 5	0.4		5	2.1		1.8	1.9		1.2		
			0/10	0.5		10	5.4		4.7	5.3		3.3		
			0/15	1.5		15	1.6		13.7	19.5		9.7		
I_{IH}, I_{IL}	Input leakage current	G, H types	0/18	Any input		18		±0.1		$±10^{-5}$	±0.1		±1	μA
		E, F types	0/15			15		±0.3		$±10^{-5}$	±0.3		±1	
I_{OZ}	3-state output	G, H types	0/18	0/18		18		±0.4		$±10^{-5}$	±0.4		±12	μA
		E, F types	0/15	0/15		15		±1.0		$±10^{-5}$	±1.0		±7.5	

PARAMETER		TEST CONDITIONS				VALUES							UNIT
		V_I (V)	V_O (V)	$\|I_O\|$ (μA)	V_{DD} (V)	T^*_{LOW} min.	T^*_{LOW} max.	25°C min.	25°C typ	25°C max.	T^*_{HIGH} min.	T^*_{HIGH} max.	
C_I	Input capacitance		Any input						5	7.5			pF

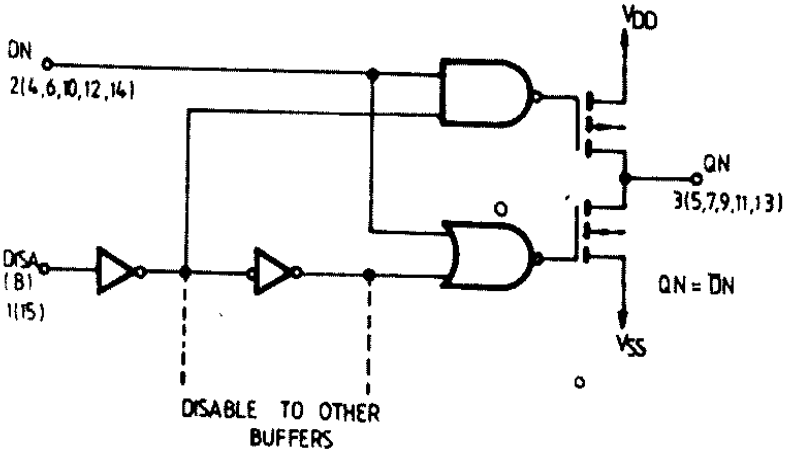
* T_{LOW} = −55°C for G, H devices; −40°C for E, F devices.
* T_{HIGH} = +125°C for G, H devices; +85°C for E, F devices.
The Noise Margin for both "1" and "0" level is:
1 V min. with V_{DD} = 5 V
2 V min. with V_{DD} = 10 V
2.5 V min. with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS

(T_A = 25°C, C_L = 50 pF, R_L = 200 k, typical temperature coefficient for all V_{DD} = 0.3%/°C values, all input rise and fall time = 20 ns)

PARAMETER		TEST CONDITIONS	VALUES			UNIT
		V_{DD}(V)	min.	typ.	max.	
t_{PLH}, t_{PHL}	Propagation delay time Low-to-High	5		75	150	ns
		10		35	70	
		15		25	50	
	High-to-Low	5		55	110	
		10		25	50	
		15		17	35	
t_{PHZ}, t_{PZH}	3—state propagation delay time	5		70	140	ns
		10		30	60	
		15		25	50	
t_{PZL}, t_{PLZ}	3—state propagation delay time	5		90	180	
		10		40	80	
		15		35	70	
t_{TLH}, t_{THL}	Transition time Low-to-High	5		50	90	ns
		10		30	45	
		15		25	35	
	High-to-Low	5		35	70	
		10		20	40	
		15		13	25	

LOGIC DIAGRAM AND TRUTH TABLE



DN	DISA(B)	QN
0	0	0
1	0	1
X	1	HIGH Z